



DXTP22040CFG

40V PNP LOW VCESAT TRANSISTOR IN PowerDI3333-8

Features

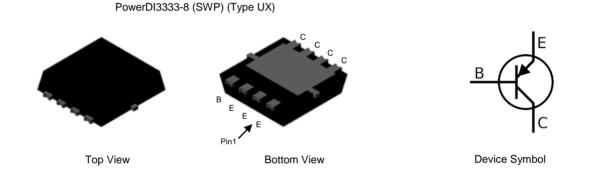
- BV_{CEO} > -40V
- Small Form Factor Thermally Efficient Package. Enables Higher Density End Products
- I_C = -2A Continuous Collector Current
- I_{CM} = -3A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < -225mV @ -1A
- Complementary NPN Type: DXTN22040CFG
- Rated to +175°C Ideal For High Temperature Environment
- Wettable Flank For Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: PowerDl[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.03 grams (Approximate)

Applications

- High-Side Switch
- Supply Line Switching
- Motor Driving



Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
DXTP22040CFG-7	2K3	7	12	2,000
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS). 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.				

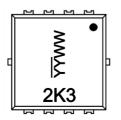
No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

PowerDI3333-8 (SWP) (Type UX)



2K3 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 19 = 2019) WW = Week Code (01 to 53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Collector-Base Voltage	V _{CBO}	-50	V	
Collector-Emitter Voltage	V _{CEO}	-40	V	
Emitter-Base Voltage	V _{EBO}	-7	V	
Continuous Collector Current	lc	-2	٨	
Peak Pulse Collector Current	I _{CM}	-3	A	
Continuous Base Current	IB	-100	mA	
Peak Pulse Base Current	I _{BM}	-200		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
	(Note 5)		1.07	W
Power Dissipation	(Note 6)	PD	2.3	W
	(Note 7)		3.4	W
	(Note 5)		140	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	R _{0JA}	65	°C/W
	(Note 7)		44	°C/W
Thermal Resistance, Junction to Leads (Note 8)	R _{θJL}	11	°C/W	
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +175	°C	

ESD Ratings (Note 9)

Characteristic		Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model		ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model		ESD MM	400	V	С
Notes: 5. For a device mounted with the collector tab on MRP FR4-PCB; device is measured under still air conditions whilst operating in a steady-state.					

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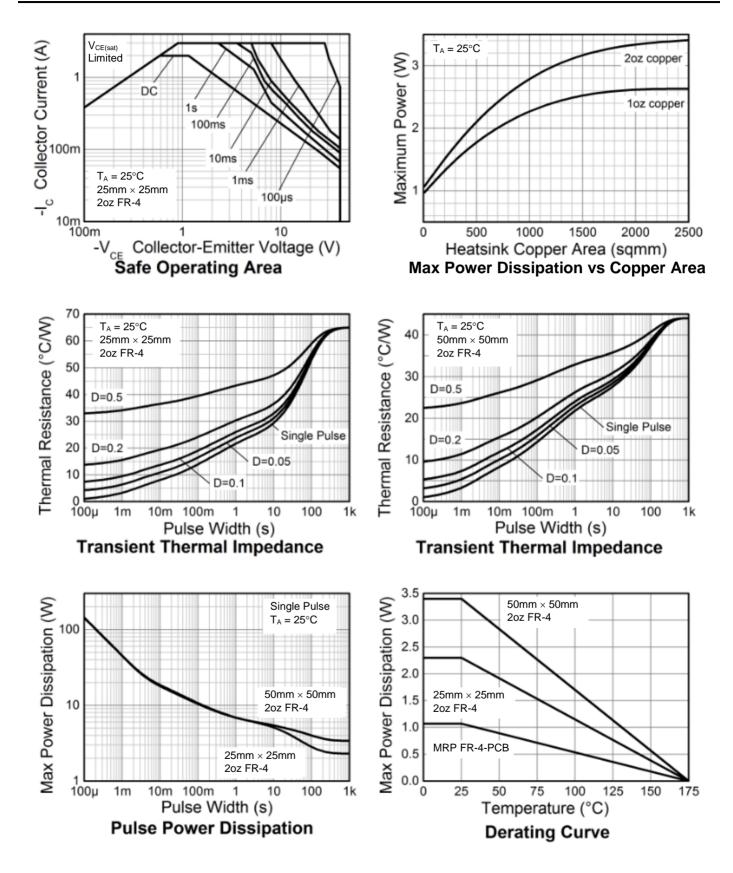
6. Same as Note 5, except the device is mounted on 25mm \times 25mm 2oz copper.

7. Same as Note 5, except the device is mounted on 50mm \times 50mm 2oz copper.

Thermal resistance from junction to solder-point (at the collector tab).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





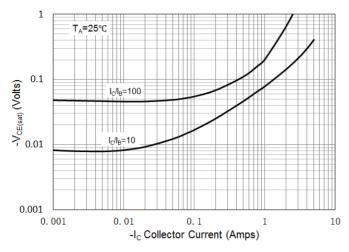
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

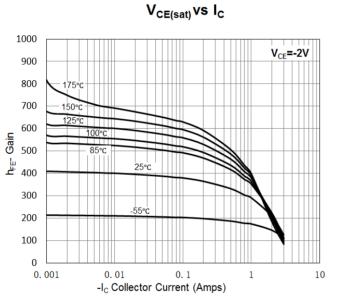
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		-50	-71	_	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CBO} BV _{CEO}	-40	-50		V	$I_{\rm C} = -10 {\rm mA}$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.6		V	I _E = -100μA
Collector-Base Cut-Off Current	lana		-1	-20	nA	V _{CB} = -50V
	I _{CBO}		-0.1	-10	μA	$V_{CB} = -40V, T_A = +150^{\circ}C$
Emitter-Base Cut-Off Current	I _{EBO}	_	-1	-20	nA	$V_{EB} = -6V$
Collector-Emitter Cut-Off Current	ICES	_	-1	-20	nA	$V_{CE} = -40V$, $V_{BE} = 0V$
Static Forward Current Transfer Ratio (Note 10)	hfe	200 200 150 80	340 299 261 196	600 —	—	$\begin{split} I_{C} &= -100 \text{mA}, \ V_{CE} = -2 \text{V} \\ I_{C} &= -500 \text{mA}, \ V_{CE} = -2 \text{V} \\ I_{C} &= -1 \text{A}, \ V_{CE} = -2 \text{V} \\ I_{C} &= -2 \text{A}, \ V_{CE} = -2 \text{V} \end{split}$
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}		-52 -42 -71 -129 -189	-100 -130 -225 -350 -600	mV	I _C = -100mA, I _B = -1mA I _C = -500mA, I _B = -50mA I _C = -1A, I _B = -100mA I _C = -2A, I _B = -200mA I _C = -3A, I _B = -300mA
Collector-Emitter Saturation Resistance (Note 10)	R _{CE(sat)}		_	225	mΩ	$I_{C} = -1A, I_{B} = -100mA$
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}		-0.88	-1	V	$I_{C} = -1A, I_{B} = -100mA$
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(on)}		-0.77	-0.9	V	$I_{C} = -1A, V_{CE} = -2V$
Transition Frequency	f⊤	—	120	—	MHz	I _C = -50mA, V _{CE} = -10V f = 100MHz
Output Capacitance	Cobo	_	12	_	pF	$V_{CB} = -10V, f = 1MHz$
	t _{delay}		11.6	_	ns	
Switching Characteristics	t _{rise}		128	_	ns	$V_{CC} = -10V, I_{C} = -500mA$
ownering onalacteristics	t _{storage}	_	524	—	ns	$I_{B1} = -I_{B2} = -50 \text{mA}$
	t _{fall}	—	69.4		ns	

Note: 10. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.

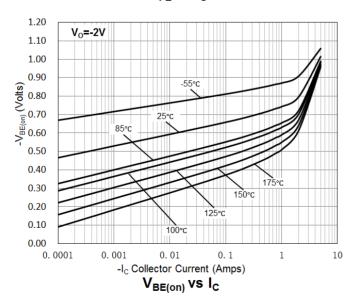


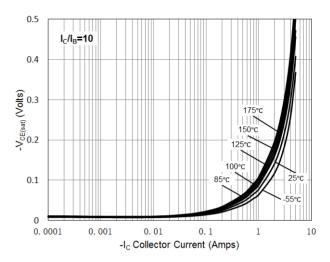
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



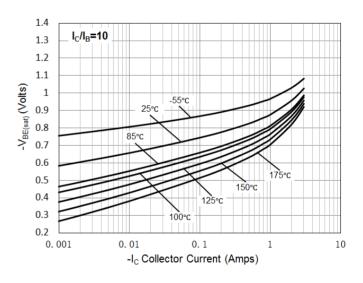








V_{CE(sat)}vs I_C



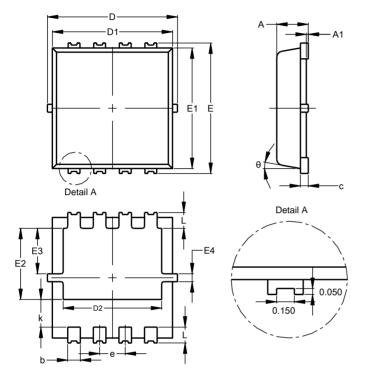
V_{BE(sat)} vs I_C



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

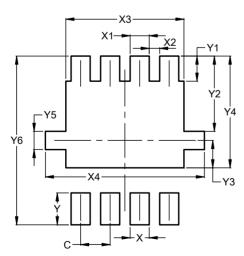


PowerDI3333-8 (SWP) (Type UX)				
Dim	Min	Max	Тур	
Α	0.75	0.85	0.80	
A1	0.00	0.05		
b	0.25	0.40	0.32	
С	0.10	0.25	0.15	
D	3.20	3.40	3.30	
D1	2.95	3.15	3.05	
D2	2.30	2.70	2.50	
E	3.20	3.40	3.30	
E1	2.95	3.15	3.05	
E2	1.60	2.00	1.80	
E3	0.95	1.35	1.15	
E4	0.10	0.30	0.20	
е	_	_	0.65	
k	0.50	0.90	0.70	
L	0.30	0.50	0.40	
θ	0°	12°	10°	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700



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